NL27WZ14

Dual Schmitt-Trigger Inverter

The NL27WZ14 is a high performance dual inverter with Schmitt−Trigger inputs operating from a 1.65 to 5.5 V supply.

Pin configuration and function are the same as the NL27WZ04, but the inputs have hysteresis and, with its Schmitt trigger function, the NL27WZ14 can be used as a line receiver which will receive slow input signals. The NL27WZ14 is capable of transforming slowly changing input signals into sharply defined, jitter−free output signals. In addition, it has a greater noise margin than conventional inverters. The NL27WZ14 has hysteresis between the positive−going and the negative−going input thresholds (typically 1 V) which is determined internally by transistor ratios and is essentially insensitive to temperature and supply voltage variations.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs and Outputs
- LVTTL Compatible − Interface Capability with 5 V TTL Logic with V_{CC} = 3 V
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Current Drive Capability is 24 mA at the Outputs
- Chip Complexity: FET = 72
- Pb−Free Packages are Available

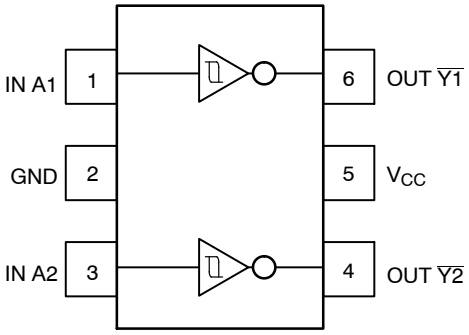

Figure 1. Pinout (Top View)

Figure 2. Logic Symbol

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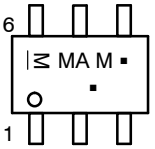
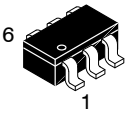
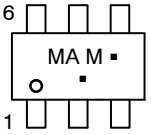
MARKING DIAGRAMS

SC−88/SOT−363/SC70−6
DF SUFFIX
CASE 419B





TSOP−6/SOT−23−6/SC59−6
DT SUFFIX
CASE 318G



MA = Device Marking
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	IN A1
2	GND
3	IN A2
4	OUT $\overline{Y2}$
5	V_{CC}
6	OUT $\overline{Y1}$

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	H
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +7.0$	V
V_O	DC Output Voltage	Output in Z or LOW State (Note 1)	$-0.5 \le V_O \le 7.0$	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	C
P_D	Power Dissipation in Still Air	SC−88, TSOP−6	200	mW
θ_{JA}	Thermal Resistance	SC−88, TSOP−6	333	C/W
T_L	Lead Temperature, 1 mm from case for 10 s		260	C
T_J	Junction Temperature under Bias		+150	C
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A
3. Tested to EIA/JESD22−A115−A
4. Tested to JESD22−C101−A

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	(High or LOW State)	0	5.5	V
T_A	Operating Free−Air Temperature		−55	+125	C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ±0.2 V V_{CC} =3.0 V ±0.3 V V_{CC} =5.0 V ±0.5 V	0 0 0	No Limit No Limit No Limit	ns/V

ORDERING INFORMATION

Device	Package	Shipping†
NL27WZ14DFT2	SC−88/SOT−363/SC70−6	3000 / Tape & Reel
NL27WZ14DFT2G	SC−88/SOT−363/SC70−6 (Pb−Free)	
NL27WZ14DTT1	TSOP−6/SOT−23−6/SC59−6	
NL27WZ14DTT1G	TSOP−6/SOT−23−6/SC59−6 (Pb−Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25 C			−40 C ≤ T_A ≤ 85 C		−55 C ≤ T_A ≤ 125 C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_T+	Positive Input Threshold Voltage		2.3 2.7 3.0 4.5 5.5	1.0 1.2 1.3 1.9 2.2	1.5 1.7 1.9 2.7 3.3	1.8 2.0 2.2 3.1 3.6	1.0 1.2 1.3 1.9 2.2	1.8 2.0 2.2 3.1 3.6	1.0 1.2 1.3 1.9 2.2	1.8 2.0 2.2 3.1 3.6	V
V_T-	Negative Input Threshold Voltage		2.3 2.7 3.0 4.5 5.5	0.4 0.5 0.6 1.0 1.2	0.75 0.87 1.0 1.5 1.9	1.15 1.4 1.5 2.0 2.3	0.4 0.5 0.6 1.0 1.2	1.15 1.4 1.5 2.0 2.3	0.4 0.5 0.6 1.0 1.2	1.15 1.4 1.5 2.0 2.3	V
V_H	Input Hysteresis Voltage		2.3 2.7 3.0 4.5 5.5	0.25 0.3 0.4 0.6 0.7	0.75 0.83 0.93 1.2 1.4	1.1 1.15 1.2 1.5 1.7	0.25 0.3 0.4 0.6 0.7	1.1 1.15 1.2 1.5 1.7	0.25 0.3 0.4 0.6 0.7	1.1 1.15 1.2 1.5 1.7	V
V_{OH}	High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA I_{OH} = −3 mA I_{OH} = −8 mA I_{OH} = −12 mA I_{OH} = −16 mA I_{OH} = −24 mA I_{OH} = −32 mA	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V_{CC} − 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V_{CC} 1.52 2.1 2.4 2.7 2.5 4.0		V_{CC} − 0.1 1.29 1.9 2.2 2.4 2.3 3.8		V_{CC} − 0.1 1.29 1.8 2.1 2.3 2.2 3.7		V
V_{OL}	Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA I_{OL} = 4 mA I_{OL} = 8 mA I_{OL} = 12 mA I_{OL} = 16 mA I_{OL} = 24 mA I_{OL} = 32 mA	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.4 0.5 0.5 0.55 0.65	V
I_{IN}	Input Leakage Current	V_{IN} = V_{CC} or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{OFF}	Power Off−Output Leakage Current	V_{OUT} = 5.5 V	0			1		10		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			1		10		10	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25 C			−40 C ≤ T_A ≤ 85 C		−55 C ≤ T_A ≤ 125 C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Input A to Y (Figure 3 and 4)	R_L = 1 MΩ, C_L = 15 pF	2.5 ± 0.2	1.8	4.3	7.4	1.8	8.1	1.8	9.1	ns
		R_L = 1 MΩ, C_L = 15 pF R_L = 500 Ω, C_L = 50 pF	3.3 ± 0.3	1.5 1.8	3.3 4.0	5.0 6.0	1.5 1.8	5.5 6.6	1.5 1.8	6.5 7.6	
		R_L = 1 MΩ, C_L = 15 pF R_L = 500 Ω, C_L = 50 pF	5.0 ± 0.5	1.0 1.2	2.7 3.2	4.1 4.9	1.0 1.2	4.5 5.4	1.0 1.2	5.5 6.4	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} =5.5 V, V_I = 0 V or V_{CC}	2.5	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_I = 0 V or V_{CC}	11 12.5	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no−load dynamic power consumption; P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

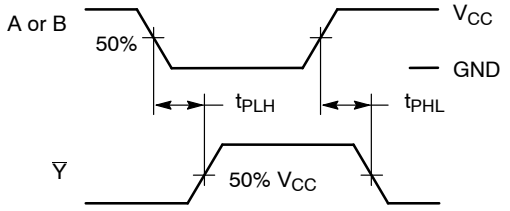
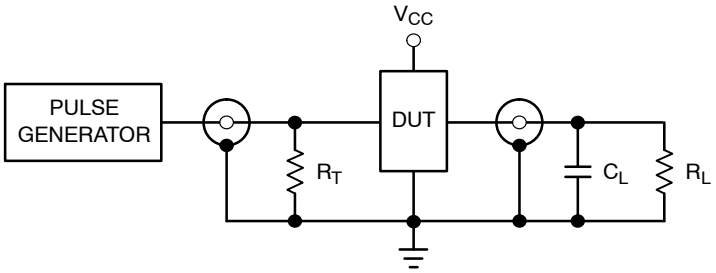


Figure 3. Switching Waveforms



R_T = C_L or equivalent (includes jog and probe capacitance)
R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

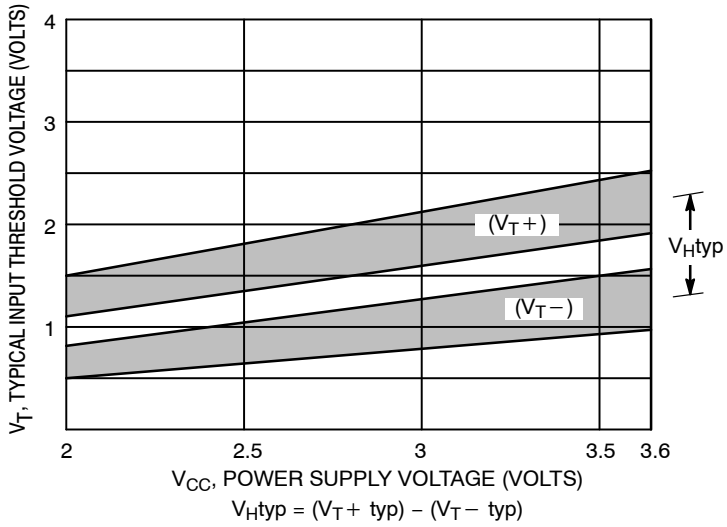
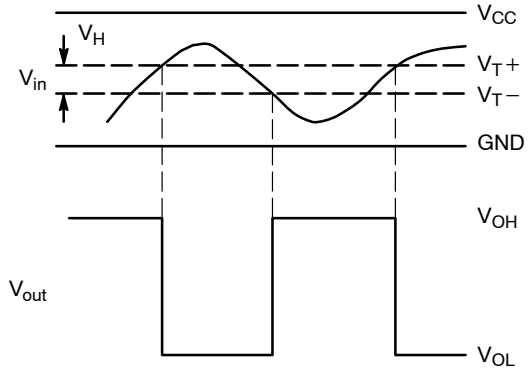
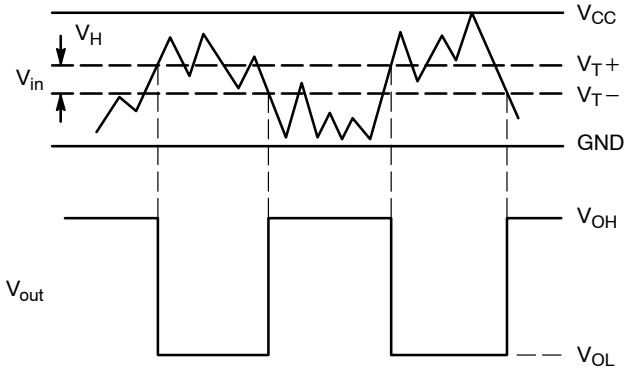


Figure 5. Typical Input Threshold, V_T+, V_T- versus Power Supply Voltage



(a) A Schmitt−Trigger Squares Up Inputs With Slow Rise and Fall Times

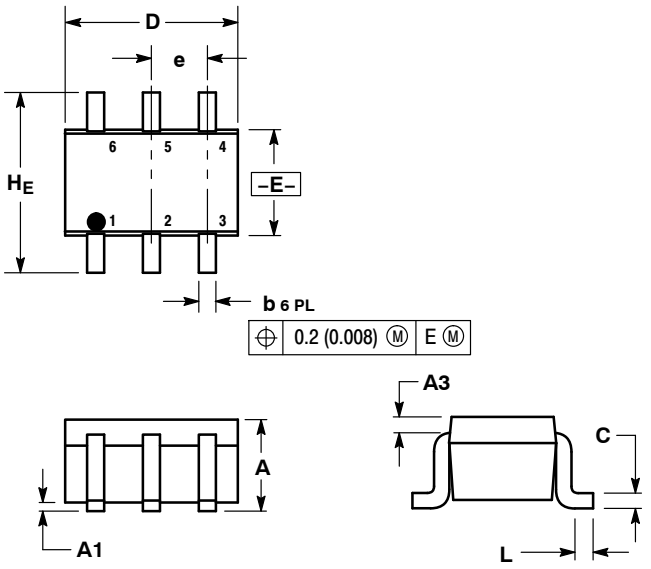


(b) A Schmitt−Trigger Offers Maximum Noise Immunity

Figure 6. Typical Schmitt−Trigger Applications

PACKAGE DIMENSIONS

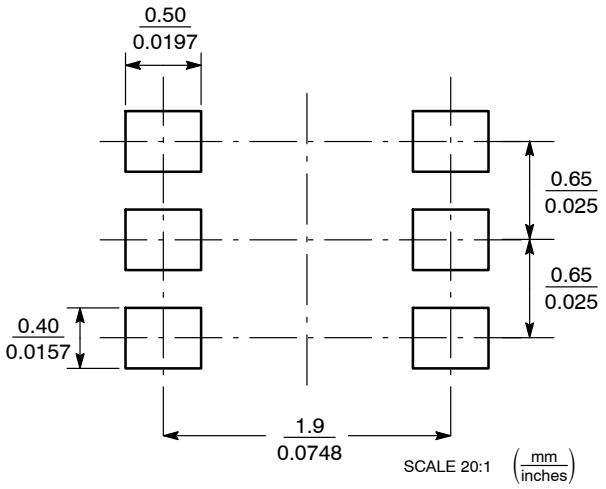
SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE W



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B−01 OBSOLETE, NEW STANDARD 419B−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	2.00	2.10	2.20	0.078	0.082	0.086

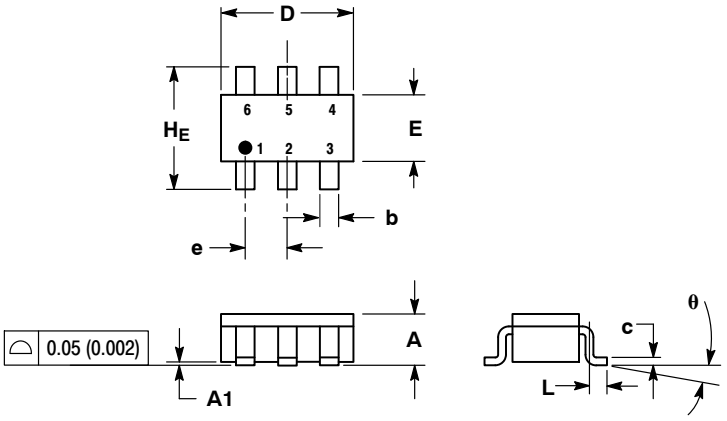
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

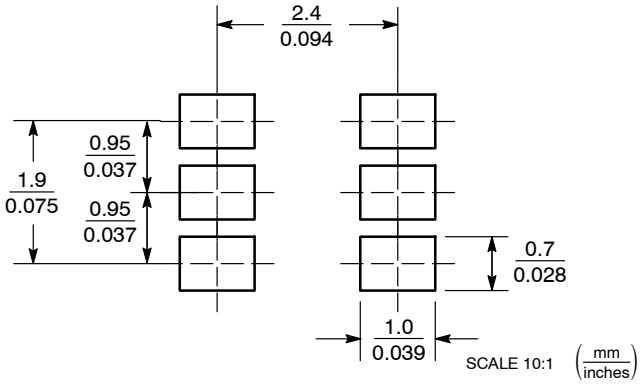
TSOP−6
CASE 318G−02
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0	–	10	0	–	10

SOLDERING FOOTPRINT*



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